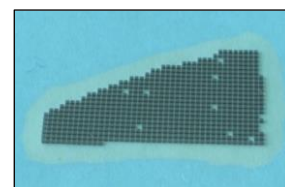




ELC-470-34E

- Blue LED bare chip die
- 470 nm, 400 mcd
- 300 x 200 x 110 μm
- GaN structure
- P + N side up



Description



ELC-470-34E is a blue LED bare chip die, based on sapphire substrate with GaN epitaxial layers, 300x200 μm , with 68 μm Au alloy bonding pads. It is typically emitting at 470 nm with a luminous intensity of 400 mcd @ 20 mA. **ELC-470-34E** is available with a MOQ of 100 pcs, and comes packed on adhesive film with wire-bond side on top. It is suitable for epoxy bonding.

Maximum Ratings*

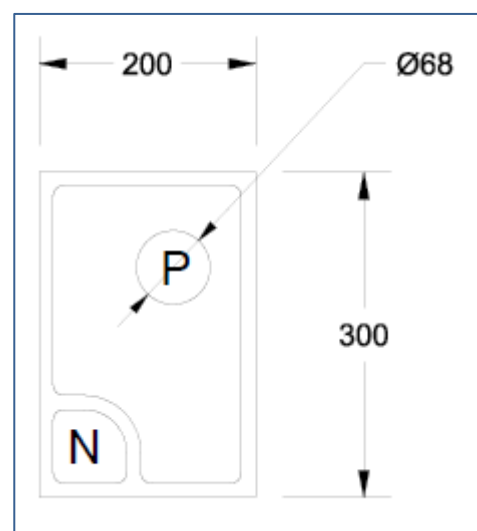
Parameter	Symbol	Values		Unit
		Min.	Max.	
Forward Current	I_F		30	mA
Reverse Voltage	U_R		5	V
Junction Temperature	T_J		+ 115	$^{\circ}\text{C}$
Operating Temperature	T_O	- 40	+ 85	$^{\circ}\text{C}$
Storage Temperature	T_{ST}	- 20	+ 65	$^{\circ}\text{C}$

* Operating close to or exceeding these parameters may damage the device.

Electro-Optical Characteristics* ($T_{CASE} = 25^{\circ}\text{C}$, $I_F = 20\text{ mA}$)

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Dominant Wavelength	λ_D	466	470	473	nm
Spectral Width (FWHM)	$\Delta\lambda$		25		nm
Forward Voltage	U_F		3.0	3.5	V
Reverse Current ($U_R = 5\text{V}$)	U_R			2	μA
Luminous Intensity	I_e		400		mcd

* $t_{TEST} < 60\text{ ms}$



dimensions $\pm 40\ \mu\text{m}$

